

1. (Currently amended) A method of fabricating a field-effect transistor device on an integrated circuit, comprising the steps of:
providing a single-crystal silicon substrate;
forming a metal silicate dielectric layer on the substrate; and
forming a conductive transistor gate overlying the metal silicate dielectric layer.

2. - 30. (canceled).

31. - 35. (canceled).

36. - 40. (canceled).

41. - 45. (canceled).

46. (currently amended, with rejoinder requested) A method of fabricating a field-effect transistor device on an integrated circuit, comprising the steps of:

providing a single-crystal silicon substrate;
forming a zirconium silicate dielectric layer on the substrate; and
forming a conductive transistor gate overlying the zirconium silicate dielectric layer.

47. - 70. (canceled).

71. (withdrawn, with rejoinder requested) The method of claim 46, wherein the forming a zirconium silicate dielectric layer step comprises:

exposing a clean Si surface on the substrate; and
depositing a partially reduced zirconium silicate layer on the Si surface.

72. (withdrawn, with rejoinder requested) The method of claim 71, further comprising annealing the partially reduced zirconium silicate layer substrate in oxygen, thereby forming the zirconium silicate dielectric layer.

73. (**withdrawn, with rejoinder requested**) The method of claim 72, wherein the depositing a partially reduced zirconium silicate layer on the Si surface comprises simultaneous physical vapor deposition of zirconium oxide and silicon.

74. - 80. (canceled).